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Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp. Customer Support Dept. April 1, 2003



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The HD74LS273, positive-edge-triggered flip-flops utilize LS TTL circuitry to implement D-type flip-flop logic with a direct clear input.

Information at the D inputs meeting the setup time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse.

Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse.

When the clock input is at either the high or low level, the D input signal has no effect at the output.

Notes;

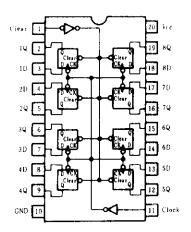
FUNCTION TABLE

	Output		
Clear	Clock	D	Q
L	×	×	L
н	t	Н	Н
н	t	L	L
Н	L	×	Q_0

H = high level, L = low level, X = irrelevant

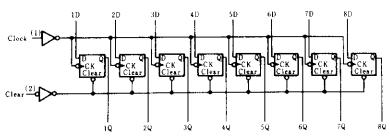
t = transition from low to high level Q₀ = level of Q before the indicated steady-state input conditions were established.

PIN ARRANGEMENT



(Top View)





ERECOMMENDED OPERATING CONDITIONS

	Item	Symbol	min	typ	max	Unit	
Supply voltage		Vci	4.75	5.00	5.25	V	
		Іоя	-		-400	μA	
Output	current	Int	_	•	8	mA	
Clock frequency		felock	0		30	MHz	
Clock	and clear pulse width	tw	20		—	ns	
Setup	Data		20 f	—	_		
time	Clear inactive-state	t en	25 t	<u></u> -	_	ns	
Data hold time		t.	5 †	· _	_	ns	

Note) † : The arrow indicates the rising edge of clock pulse.

ELECTRICAL	CHARACTERISTICS	$(Ta = -20 \sim +75^{\circ}C)$
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Item	Symbol	Test Cond	itions	min	typ*	max	Unit
	Vin			2.0			V
Input voltage	Vit					0.8	V
····	Von	$V_{cc} = 4.75V, V_{ll} = 2V, V_{lL} = 0.$	8V, Ion400μA	2.7			v
Output voltage		$V_{cc} = 4.75 \text{V}, V_{IH} = 2 \text{V},$	101-8mA		_	0.5	v
	V_{0L} $V_{1L} = 0.8V$	$V_{1L} = 0.8V$	$I_{OL} = 4 \text{mA}$	-	_	0.4	i
	$I_i = V_{cc} - 5.25V, V_i - 7V$			-		0.1	mА
Input current	I _{IN}	$V_{cc} = 5.25 V, V_l = 2.7 V$		T –	-	20	μA
	In	$V_{cc} = 5.25 \text{V}, V_{f} = 0.4 \text{V}$				-0.4	mA
Short-circuit output current	Ins	$V_{cc} = 5.25 V$		-20	-	-100	mA
Supply current	Icc**	$V_{cc} = 5.25 V$		-	17	27	mA
Input clamp voltage	Vir	$V_{cc} = 4.75 \text{V}, \ I_{IN} = -18 \text{mA}$			_	-1.5	v

* VCC=5V, Ta=25°C

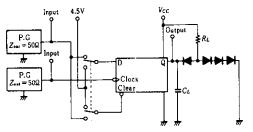
•* : With all outputs open and 4.5V applied to all data and clear inputs, I_{CC} is measured after a momentary ground, then 4.5V is applied to clock.

ESWITCHING CHARACTERISTICS ($V_{cc} = 5V$, $Ta = 25^{\circ}C$)

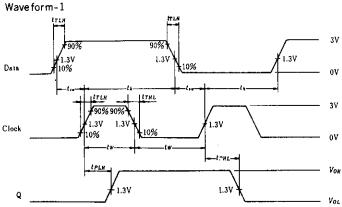
Item	Symbol	Inputs	Test Conditions	min	typ	max	Unit
Maximum clock frequency	∫ mex	Clock		30	—	—	MHz
	t _{PHL}	Clear			18	27	
Propagation Delay Time	1 PLH		$C_L = 15 \text{pF}, R_L = 2 \text{k}\Omega$		17	27	ns
	t _{PHL}	Clock		-	18	27	

Waveform-2

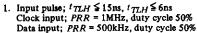
TESTING METHOD

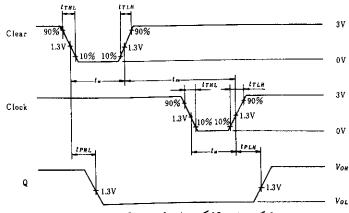


Notes: 1. C_L includes probe and jig capacitance. 2. All diodes are 1S2074 Θ .



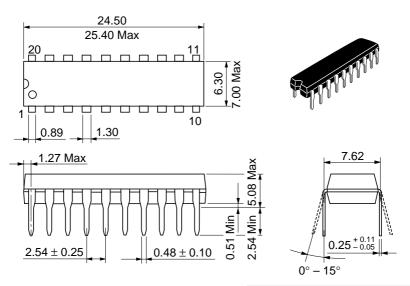






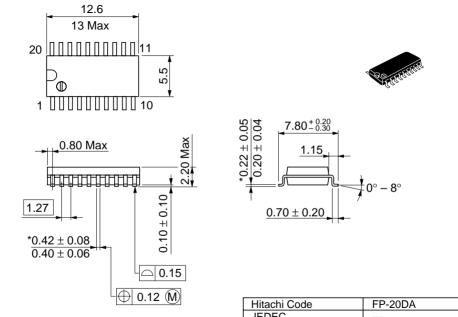
Note: Input pulse; $t_{TLH} \leq 15$ ns, $t_{THL} \leq 6$ ns, PRR = 1 MHz.

Unit: mm



Hitachi Code	DP-20N
JEDEC	_
EIAJ	Conforms
Weight (reference value)	1.26 g

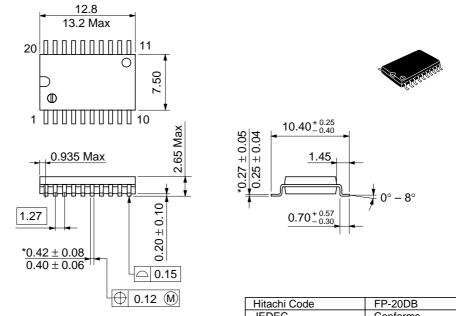
Unit: mm



*Dimension including the plating thickness Base material dimension

Hitachi Code	FP-20DA
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.31 g

Unit: mm



*Dimension including the plating thickness Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

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